

MOSFET - Power, Single N-Channel, STD Gate, μ 8FL

40 V, 4.9 m Ω , 65 A

NTTFS4D9N04XM

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (3.3 x 3.3 mm) for Compact Design
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Motor Drive
- Battery Protection
- Synchronous Rectification

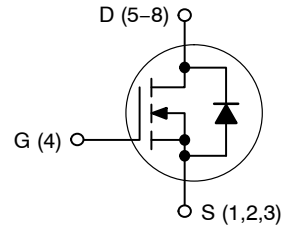
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	DC V_{GS}	± 20	V
Continuous Drain Current	I_{DA}	$T_C = 25^\circ\text{C}$	65
		$T_C = 100^\circ\text{C}$	46
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	38
Continuous Drain Current $R_{\theta JA}$	I_D	$T_A = 25^\circ\text{C}$	18
		$T_A = 100^\circ\text{C}$	13
Pulsed Drain Current	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	390
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	32	A
Single Pulse Avalanche Energy ($I_{PK} = 10 \text{ A}$)	E_{AS}	27	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

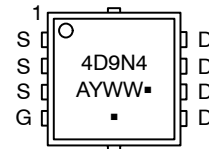
$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	4.9 m Ω @ $V_{GS} = 10 \text{ V}$	65 A

N-CHANNEL MOSFET



WDFN8
(μ 8FL)
CASE 511AB

MARKING DIAGRAM



4D9N4 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTTFS4D9N04XM

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.91	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	$R_{\theta JA}$	48.3	

- Surface-mounted on FR4 board using 650 mm², 2 oz Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$			10	μA
		$V_{DS} = 40\text{ V}, T_J = 125^\circ\text{C}$			100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}, T_J = 25^\circ\text{C}$		4.32	4.9	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 30\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	2.5	2.98	3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 30\text{ }\mu\text{A}$		-7.29		mV/°C
Forward Trans-conductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 10\text{ A}$		45		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}, f = 1\text{ MHz}$		668		pF
Output Capacitance	C_{OSS}			478		
Reverse Transfer Capacitance	C_{RSS}			13.5		
Output Charge	Q_{OSS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$		14.4		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DD} = 20\text{ V}; I_D = 30\text{ A}$		10.4		
Threshold Gate Charge	$Q_{G(TH)}$			2		
Gate-to-Source Charge	Q_{GS}			3.2		
Gate-to-Drain Charge	Q_{GD}			1.9		
Gate Resistance	R_G		$f = 1\text{ MHz}$		1.6	

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 20\text{ V},$ $I_D = 30\text{ A}, R_G = 0\text{ }\Omega$		12		ns
Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(OFF)}$			16.3		
Fall Time	t_f			3.8		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}, T_J = 25^\circ\text{C}$		0.8	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 10\text{ A}, T_J = 125^\circ\text{C}$		0.65		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 30\text{ A},$ $dI/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 20\text{ V}$		25		ns
Charge Time	t_a			8		
Discharge Time	t_b			17		
Reverse Recovery Charge	Q_{RR}			8.9		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NTTFS4D9N04XM

TYPICAL CHARACTERISTICS

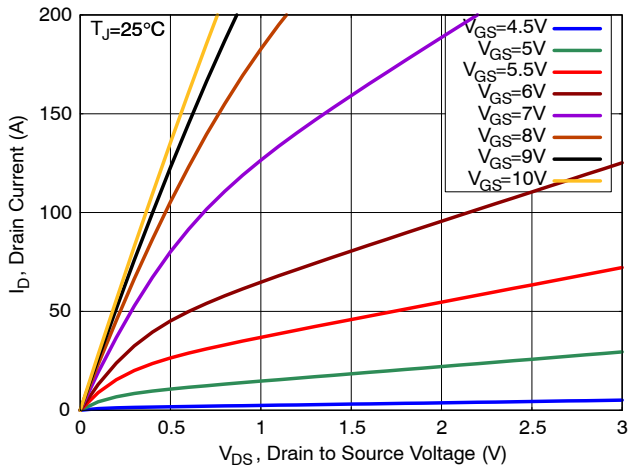


Figure 1. On-Region Characteristics

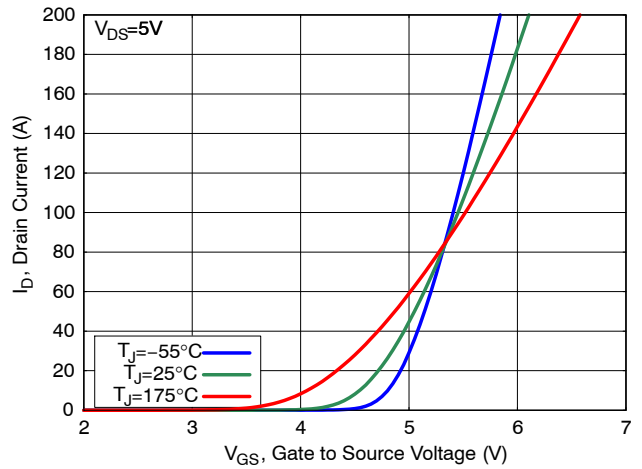


Figure 2. Transfer Characteristics

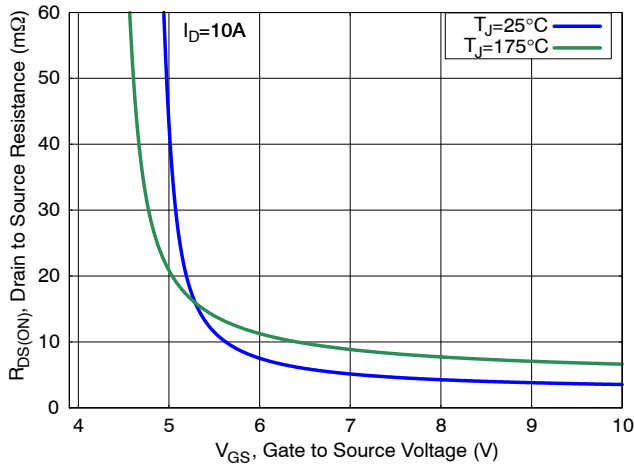


Figure 3. On-Resistance vs. Gate Voltage

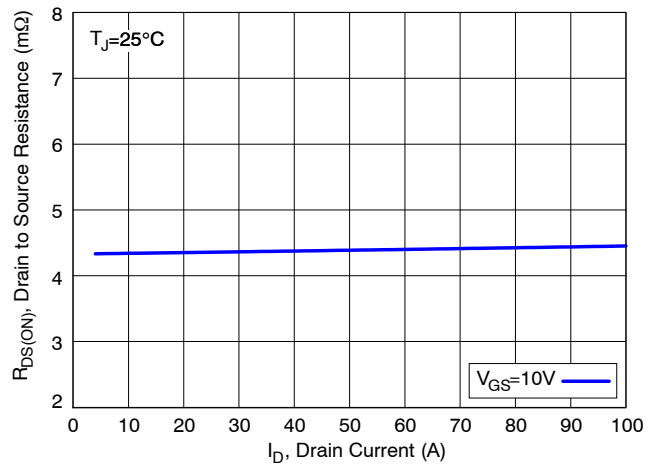


Figure 4. On-Resistance vs. Drain Current

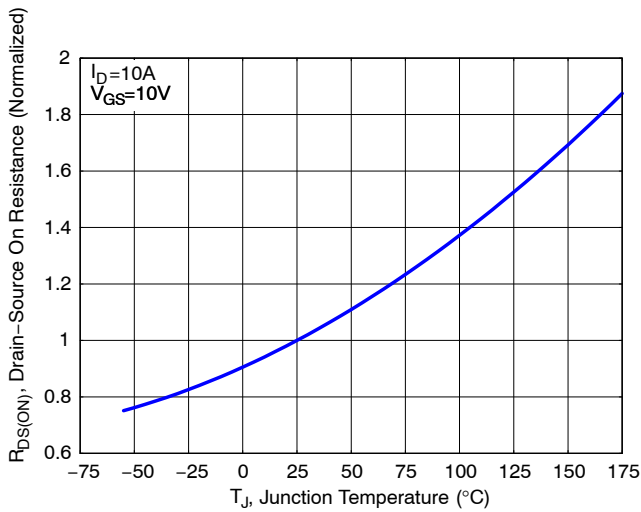


Figure 5. Normalized ON Resistance vs. Junction Temperature

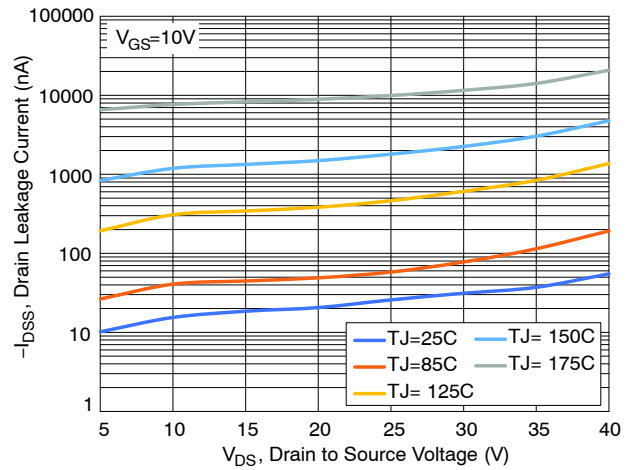


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTTFS4D9N04XM

TYPICAL CHARACTERISTICS

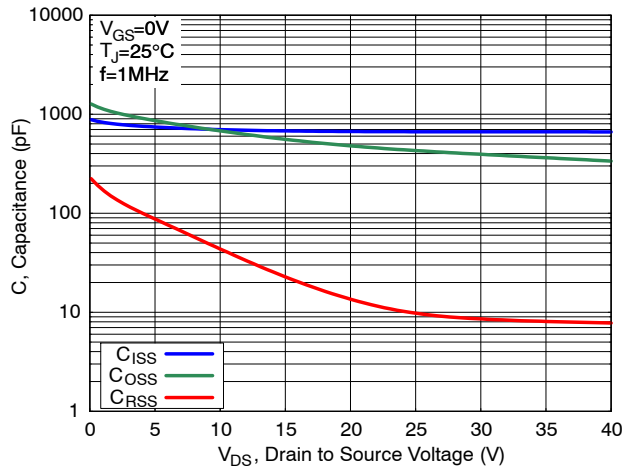


Figure 7. Capacitance Characteristics

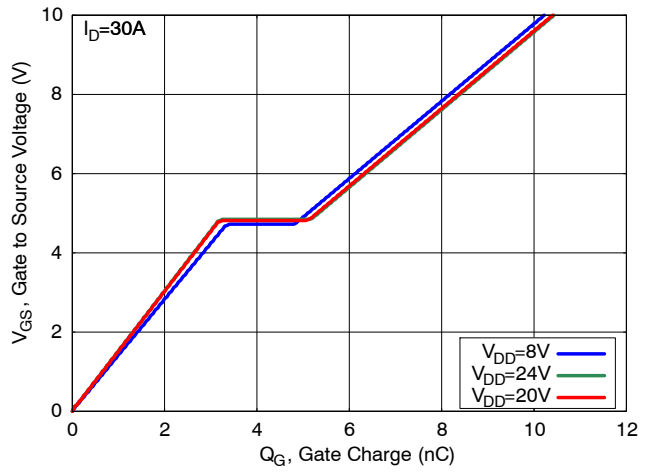


Figure 8. Gate Charge Characteristics

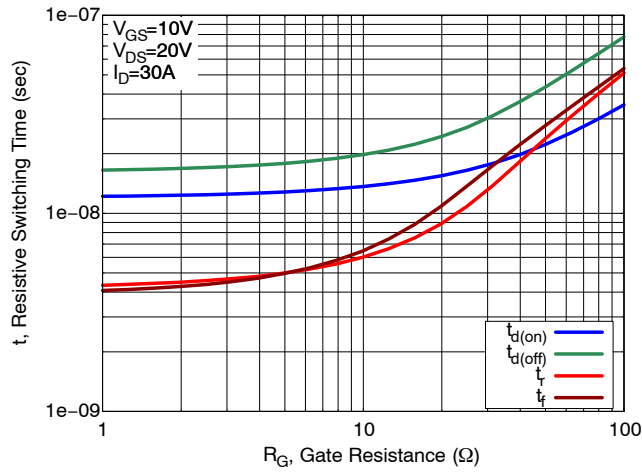


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

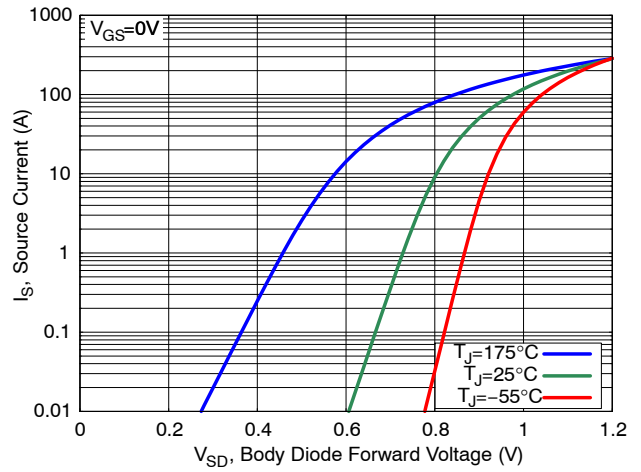


Figure 10. Diode Forward Characteristics

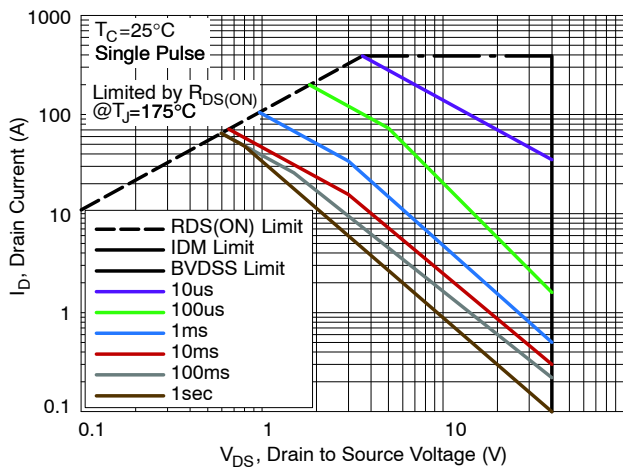


Figure 11. Safe Operating Area (SOA)

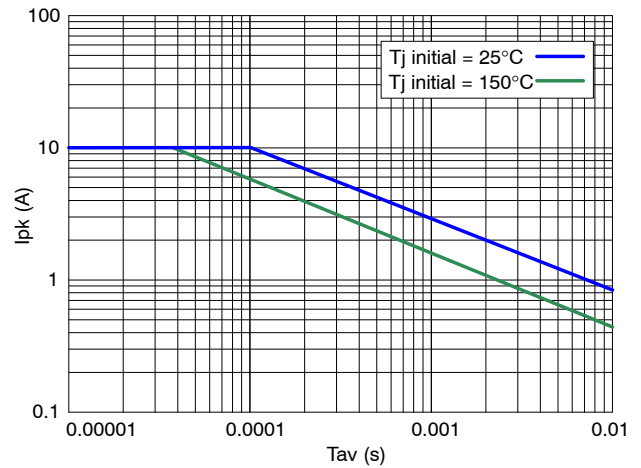


Figure 12. Avalanche Current vs. Pulse Time (UIS)

NTTFS4D9N04XM

TYPICAL CHARACTERISTICS

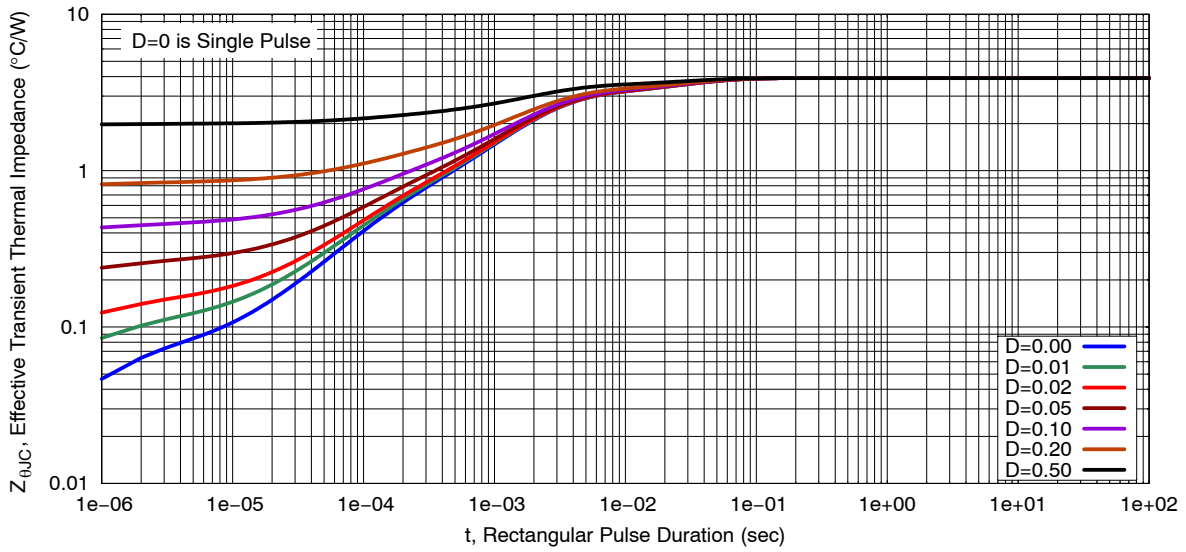


Figure 13. Transient Thermal Response

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTTFS4D9N04XMTAG	4D9N4	WDFN8 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

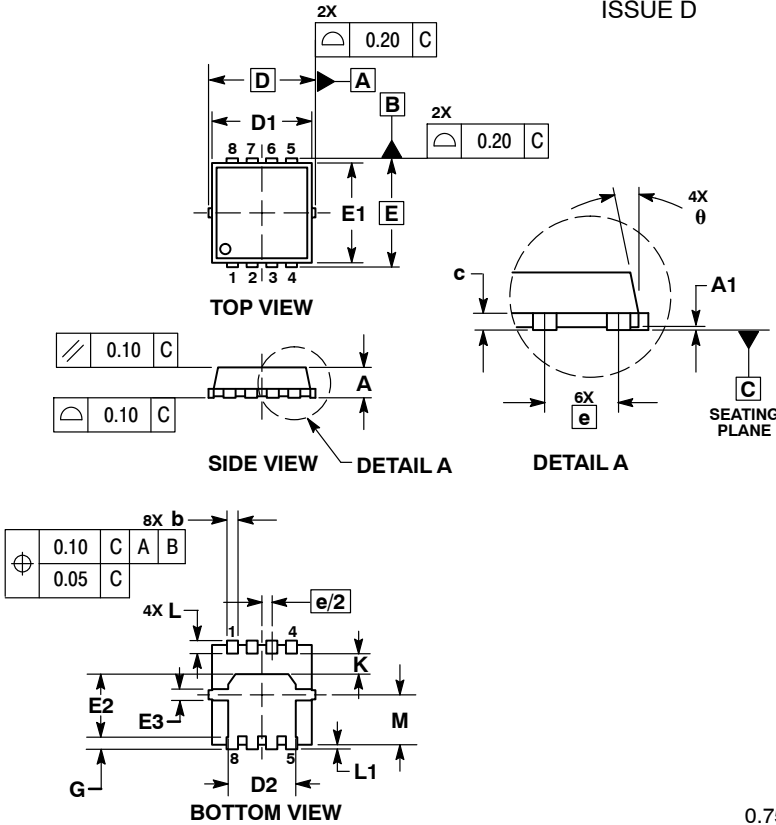
NTTFS4D9N04XM

PACKAGE DIMENSIONS

WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

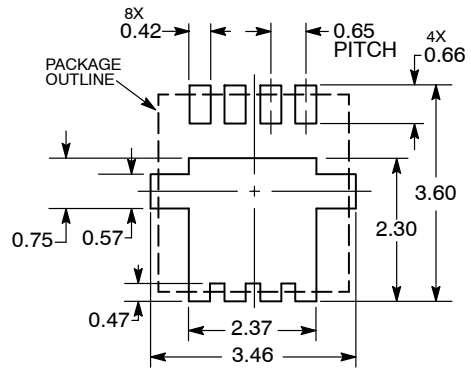
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
theta	0 °	---	12 °	0 °	---	12 °

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales